



**PNP Silicon Transistor** 

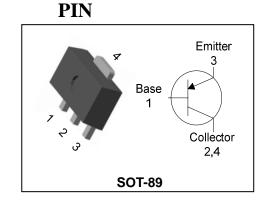
# **Description**

• Medium power amplifier

#### **Features**

- P<sub>C</sub>(Collector power dissipation)
  - =1W(Ceramic substate of 250 m² × 0.8t used)
- Low collector saturation voltage : V<sub>CE(sat)</sub>=-0.2V(Typ.)
- Complementary pair with STD1664

## **Ordering Information**



Type NO.	Marking	Package Code	
STB1132	A1 YWW	SOT-89	
A1: DEVICE CODE, YWW(Y: Year code, WW: Weekly code)			

## **Absolute maximum ratings**

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	$V_{CBO}$	-40	V
Collector-Emitter voltage	$V_{\sf CEO}$	-32	V
Emitter-Base voltage	$V_{EBO}$	-5	V
Collector current	I <sub>C</sub>	-1	А
Callagtar reguer dissination	P <sub>C</sub>	0.5	10/
Collector power dissipation	P <sub>C</sub> *	1	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~150	°C

<sup>\* :</sup> When mounted on ceramic substrate(250 mm $^2 \times 0.8t$ )

#### **Electrical Characteristics**

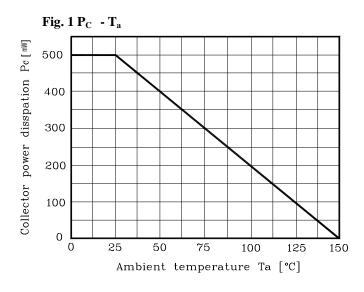
(Ta=25°C)

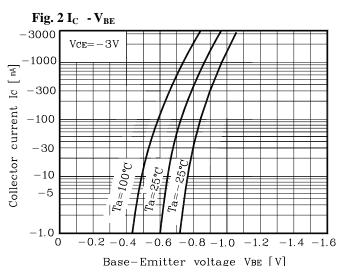
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector-Base breakdown voltage	BV <sub>CBO</sub>	$I_{C} = -50  \mu A, I_{E} = 0$	-40	-	-	V
Collector-Emitter breakdown voltage	BV <sub>CEO</sub>	$I_C=-1$ MA, $I_B=0$	-32	ı	-	V
Emitter-Base breakdown voltage	BV <sub>EBO</sub>	$I_E = -50  \mu A, I_C = 0$	-5	ı	-	V
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -20V, I_{E} = 0$	-	-	-0.1	μA
Collector cut-off current	I <sub>CES</sub>	$V_{CE} = -30V$ , $I_{C} = 0$	-	-	-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -4V$ , $I_{C} = 0$	-	-	-0.1	μA
DC current gain	h <sub>FE</sub> *	$V_{CE} = -3V$ , $I_{C} = -0.1A$	100	-	320	-
Collector-Emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$	-	-0.2	-0.8	V
Transition frequency	f <sub>T</sub>	$V_{CE}$ =-5V, $I_{C}$ =-50 mA, $f$ =30 MHz	-	150	-	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB}$ =-10V, $I_{E}$ =0, $f$ =1 MHz	_	20	30	pF

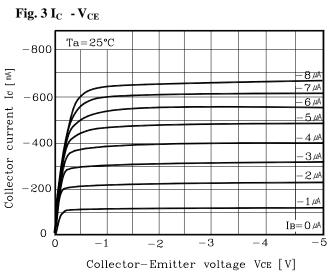
<sup>\* :</sup>  $h_{FE}$  rank / O : 100 ~ 200, Y : 160 ~ 320

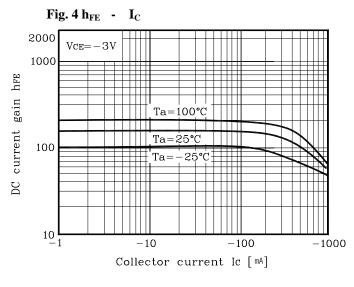
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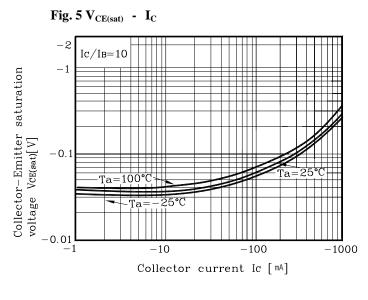
## **Electrical Characteristic Curves**

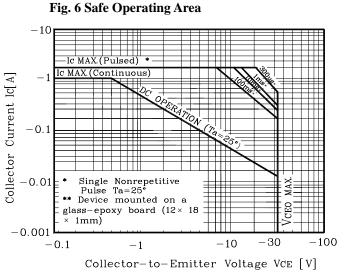






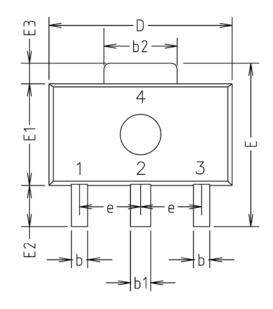


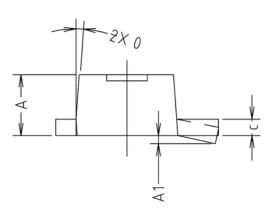




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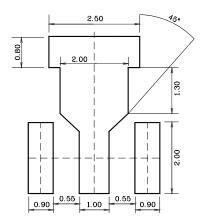
# **Outline Dimension(mm)**





	MILLIMETERS			
SYMBOL	MINIMUM	NOMINAL	MAXIMUM	NOTE
Α	1.40	1.50	1.60	
A1	0.00	_	0.10	
b	0.38	0.42	0.48	
b1	0.48	0.52	0.58	
b2	1.79	1.82	1.87	
С	0.40	0.42	0.46	
D	4.40	4.50	4.70	
Ε	3.70	4.00	4.30	
E1	2.40	2.50	2.70	
E2	0.80	1.00	1.20	
E3	0.40	0.50	0.60	
е		1.50 TYP.	·	
0		4° TYP.		

# \*Recommend PCB solder land [Unit: mm]



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